TOSHIBA PHOTOCOUPLER GaAℓAs IRED + PHOTO-IC

TLP759F

DIGITAL LOGIC GROUND ISOLATION

LINE RECEIVER

MICROPROCESSOR SYSTEM INTERFACES

SWITCHING POWER SUPPLY FEEDBACK CONTROL

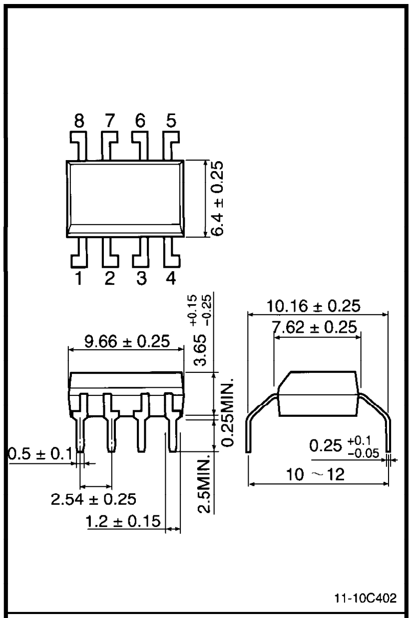
TRANSISTOR INVERTOR

The TOSHIBA TLP759F consists of a GaAℓAs high-output light emitting diode and a high speed detector of one chip photo diode-transistor. This unit is 8-lead DIP package.

TLP759F has no internal base connection, and a Faraday shield integrated on the photodetector chip provides an effective common mode noise transient immunity.

So this is suitable for application in noisy environmental condition. All parameters are tested to the specification of TLP759.

Unit in mm



TOSHIBA 11-10C402

Weight : 0.54g

- Isolation Voltage : 5000 Vrms (Min.)
- Switching Speed : $t_{pHL} = 0.3\mu s$ (Typ.)
  $t_{pLH} = 0.5\mu s$ (Typ.) ($R_L = 1.9k\Omega$)
- TTL Compatible
- UL Recognized : UL1577, File No. E67349
- Option (D4) type
  VDE Approved : DIN VDE0884 / 06.92
  Certificate No. 83676

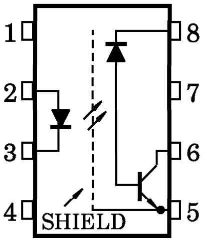
Maximum Operating Insulation : $1140V_{PK}$

Highest Permissible Over Voltage : $6000V_{PK}$

(Note) When a VDE0884 approved type is needed, please designate the “Option (D4)”

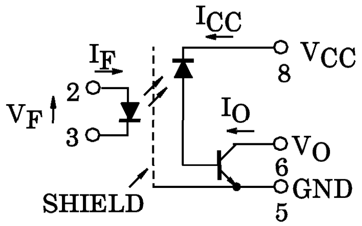
- Creepage Distance : 8.0mm
  Clearance : 8.0mm
  Insulation Thickness : 0.4mm

PIN CONFIGURATION (TOP VIEW)



1 : N.C.
2 : ANODE
3 : CATHODE
4 : N.C.
5 : EMITTER (GND)
6 : COLLECTOR (OUTPUT)
7 : N.C.
8 : V_{CC}

SCHEMATIC



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